

DB3, DB4

V_{BR} : 32 - 40 Volts

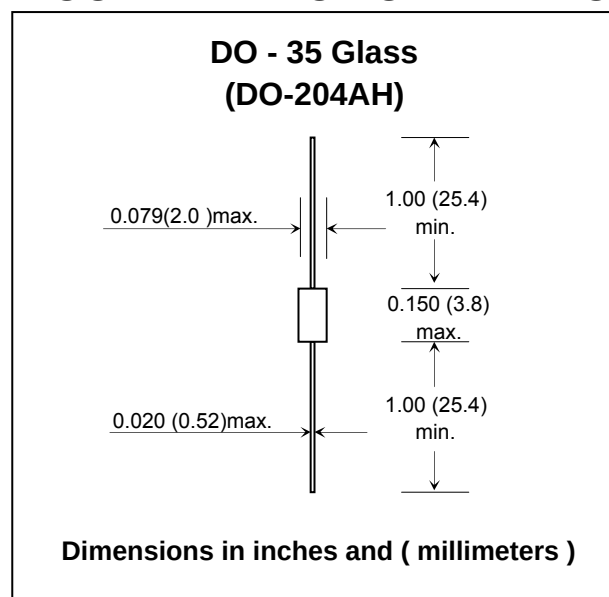
FEATURES :

- * V_{BR} : 32 V and 40 V
- * Low breakover current
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case: DO-35 Glass Case
- * Weight: approx. 0.11g

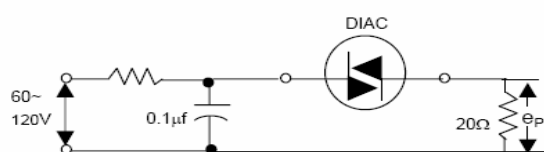
SILICON BIDIRECTIONAL DIACS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

RATING	SYMBOL	DB3	DB4	UNIT
Minimum Breakover Voltage	V_{BR1} and V_{BR2} (Min.)	28	35	V
Typical Breakover Voltage	V_{BR1} and V_{BR2} (Typ.)	32	40	V
Maximum Breakover Voltage	V_{BR1} and V_{BR2} (Max.)	36	45	V
Maximum Breakover Current	$I_{(BR)1}$ and $I_{(BR)2}$	200		μA
Maximum Breakover Voltage Symmetry	$[V_{(BR)1}] - [V_{(BR)2}]$	3.8		V
Minimum Dynamic Breakback Voltage $\Delta I = [I_{BR} \text{ to } I_F = 10 \text{ mA}]$	$ \Delta V \pm $	5.0		V
Maximum Peak Current at Ta = 50 °C (10 μs duration, 120 cycle repetition rate)	I_P	± 2		A
Maximum Peak output Voltage at Ta = 50 °C **	e_P	± 3		V
Thermal Impedance Junction to Ambient	$R_{\theta JA}$	60		°C/W
Operating Junction Temperature Range	T_J	- 40 to + 100		°C
Storage Temperature Range	T_{STG}	- 40 to + 150		°C

**CIRCUIT FOR PEAK OUTPUT VOLTAGE TEST



Characteristics at $T_{amb} = 25^\circ C$

TYPICAL DIAC-TRIAC
FULL-WAVE PHASE CONTROL CIRCUIT

